

# Characterization of Segmented Silicon Detectors for Neutron Beta Decay

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# Outline

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## 1) Introduction

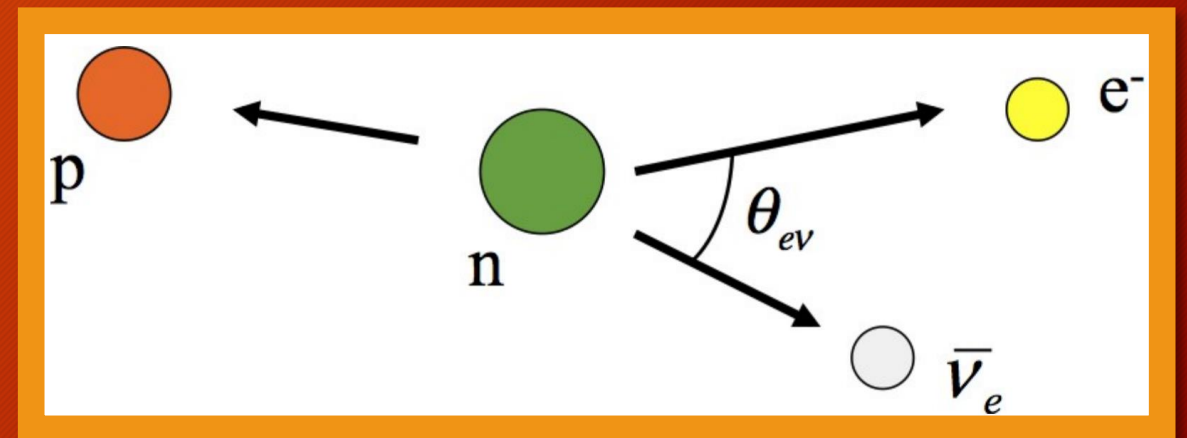
- Neutron beta decay
- The CKM matrix

## 2) Instrumentation

- The Nab experiment
- Silicon Diode Detectors
- Low-energy proton source @ MB

## 3) Characterization

- Proton spot size study
- Detector optimization



# Theory - Neutron Beta Decay

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$$\frac{d\Gamma}{dE_e d\Omega_e d\Omega_\nu} = \frac{1 + 3\lambda^2}{(4\pi)^5 \hbar} |V_{ud}|^2 g_v^2 \left(\frac{g_w}{M_w}\right)^4 p_e E_e (E_0 - E_e)^2$$
$$\times \left( 1 + a \frac{\vec{p}_\nu \cdot \vec{p}_e}{E_\nu E_e} + b \frac{m_e}{E_e} + \vec{\sigma}_n \cdot \left( A \frac{\vec{p}_e}{E_e} + B \frac{\vec{p}_\nu}{E_\nu} \right) + \dots \right)$$

J. D. Jackson et. al. Phys. Rev. 106 (1957)

- Determine “little-a” from experiment (e-ν momentum correlation)
- Extract  $\lambda$  - the mixing of axial vector to vector coupling in the weak interaction

$$a = \frac{1 - |\lambda|^2}{1 + 3|\lambda|^2}$$

# Theory - The CKM Matrix

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- $\lambda$  and  $\tau_n$  give rise to  $V_{ud}$
- CKM matrix unitarity highly dependent on  $V_{ud}$
- Unitarity of CKM speaks to the number of possible quark generations
- $3\sigma$  away from the expected value of 1

$$|V_{ud}|^2 = \frac{(4908.7 \pm 1.9) \text{ s}}{\tau_n (1 + 3\lambda^2)}$$

$$\begin{pmatrix} d' \\ s' \\ b' \end{pmatrix} = \begin{pmatrix} V_{ud} & V_{us} & V_{ub} \\ V_{cd} & V_{cs} & V_{cb} \\ V_{td} & V_{ts} & V_{tb} \end{pmatrix} \cdot \begin{pmatrix} d \\ s \\ b \end{pmatrix}$$

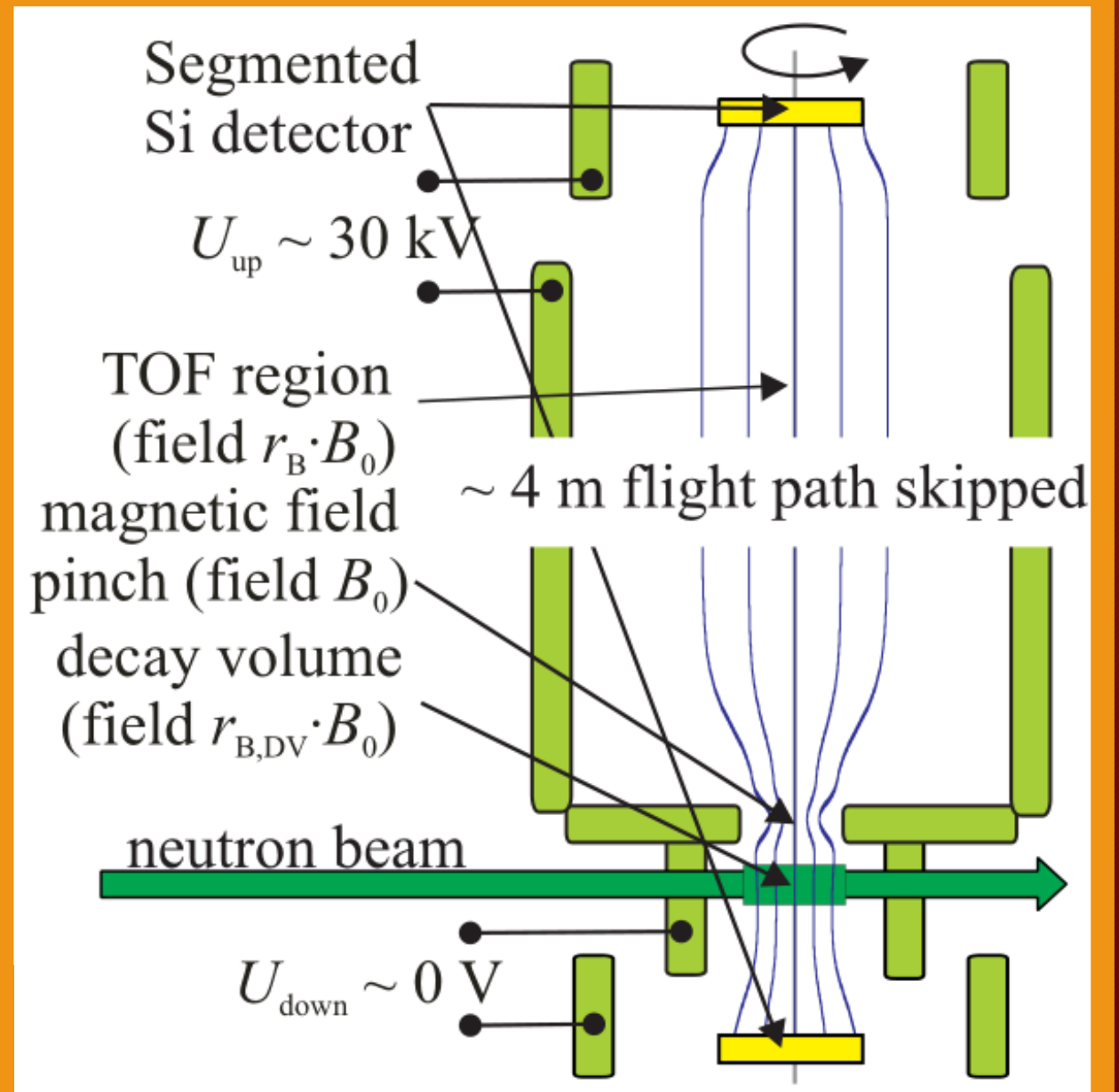
Ideally:

$$|V_{ud}|^2 + |V_{us}|^2 + |V_{ub}|^2 = 1$$

# The Nab Experiment

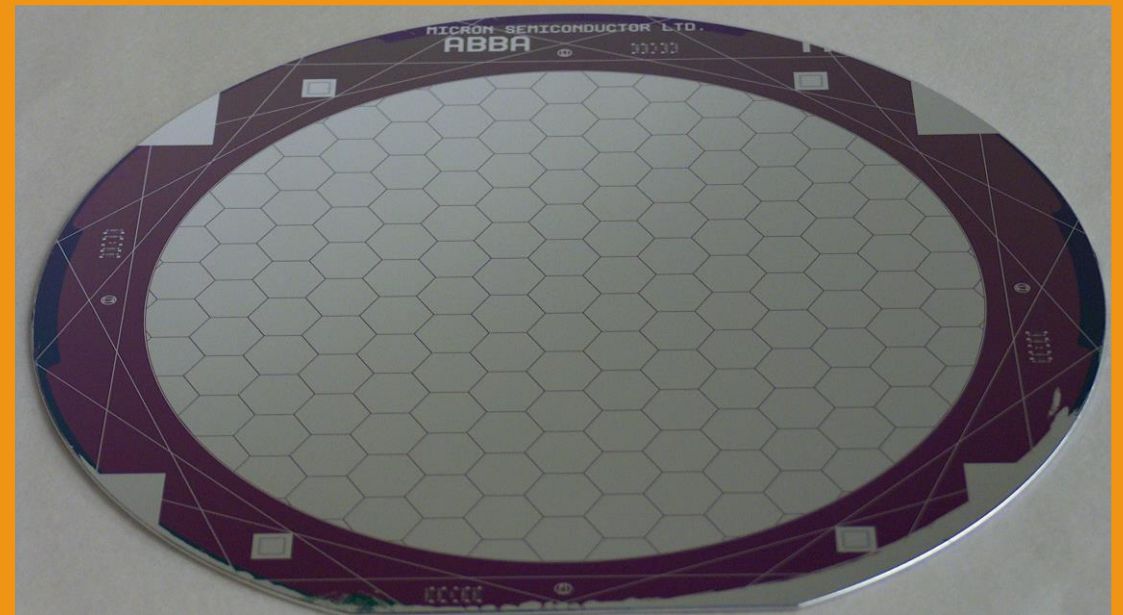
- Spalled neutrons spontaneously decay
- Time-of-Flight Spectrometer
- Measure a and b via electron energy and proton momentum
- Uses well-characterized silicon diode detectors

Salas-Bacci et. al.,  
Nuclear  
Instruments and  
Methods (2014)

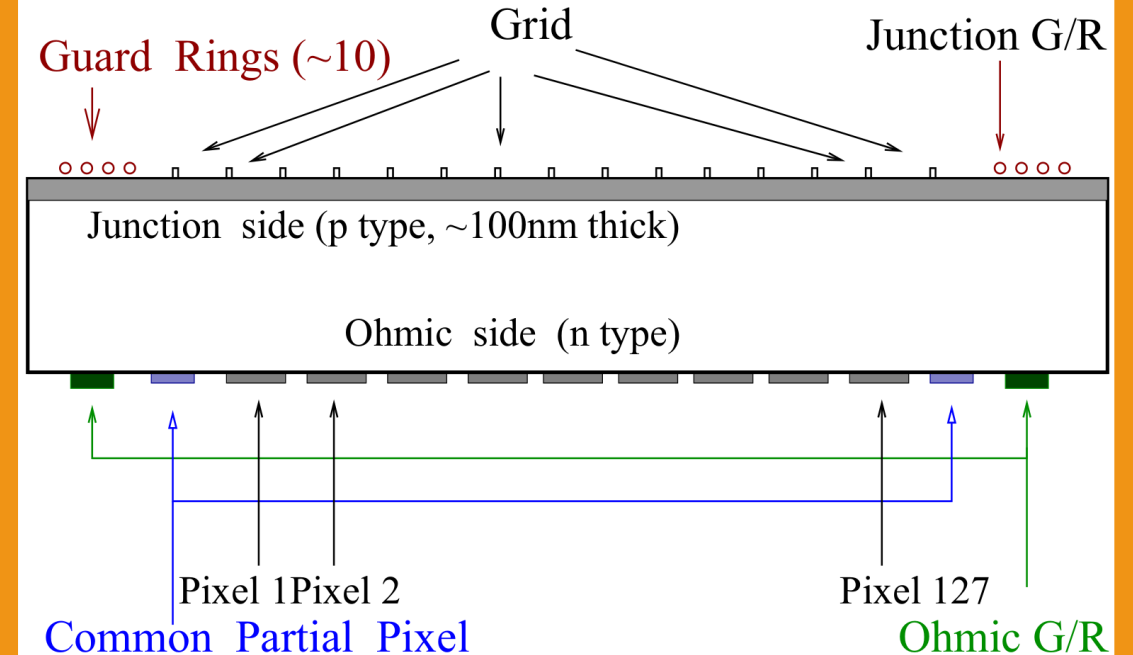


# Silicon Diode Detectors

- Layered silicon semiconductor
- Dopants added to increase/decrease charge carriers
- Reverse DC Bias applied across the junction
- Charged particle lodges in the depleted region

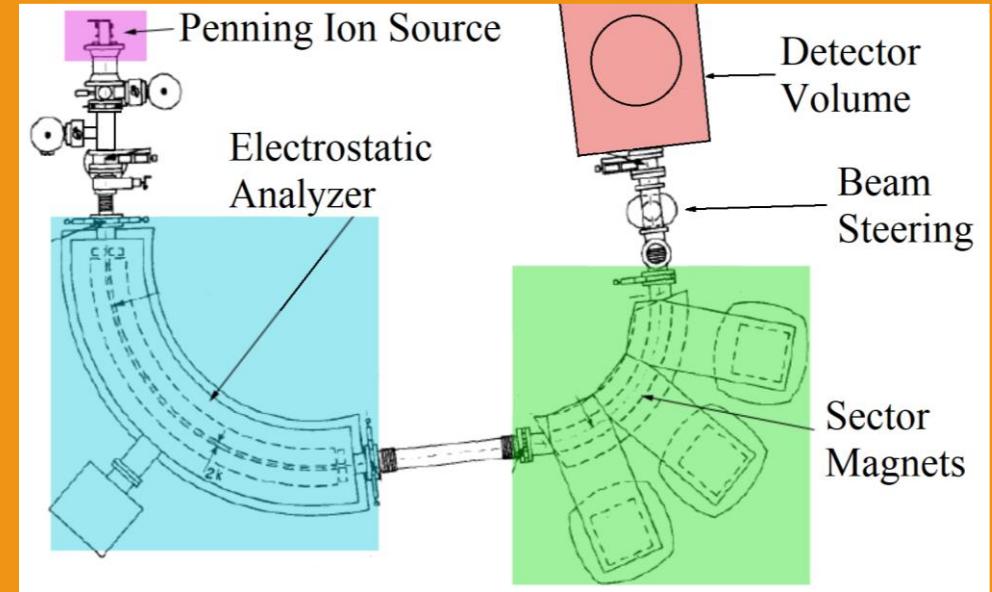


Courtesy of the Nab collaboration



# Experimental Setup

- Manitoba II proton source (ex-mass spec)
- Consists of:
  - Penning Ion Source (H-Ar)
  - Energy filtering (ESA)
  - Momentum filtering (Sector Magnets)
  - Beam steering apparatus



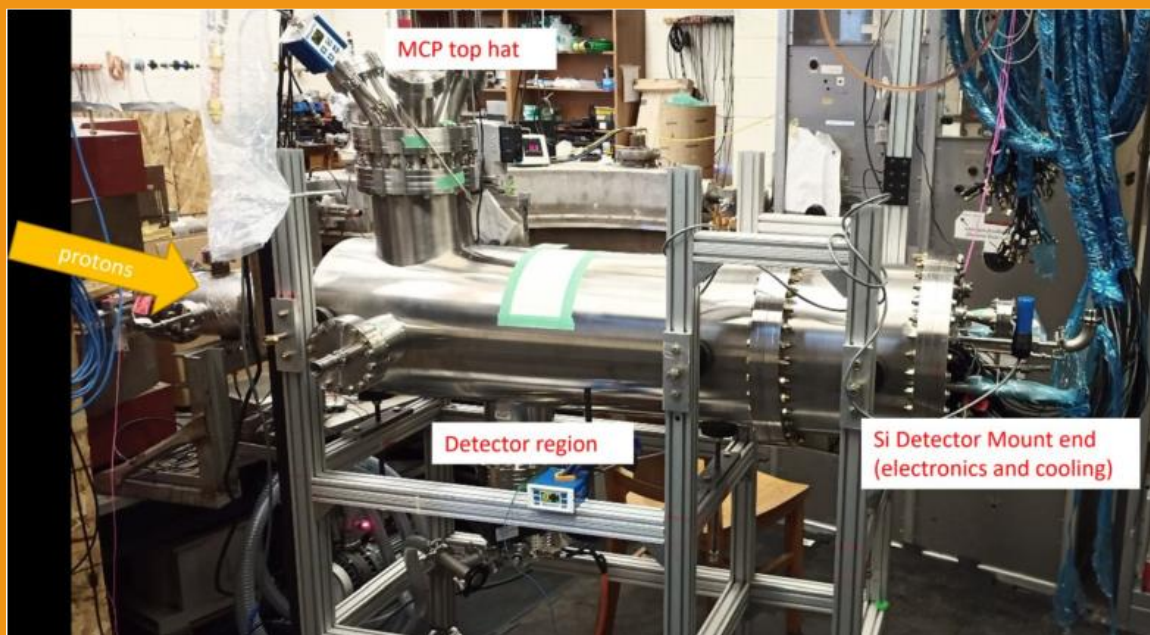
D. Harrison M.Sc Thesis (2013) modified



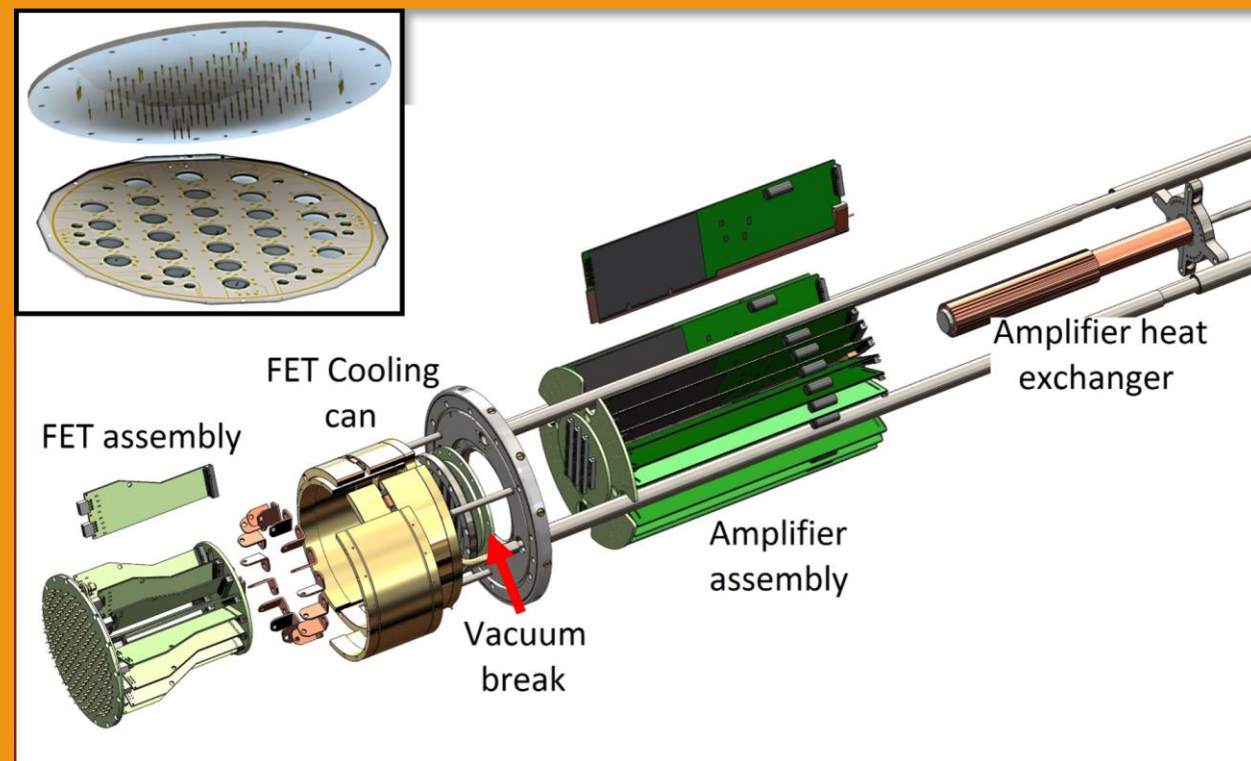
Courtesy of R. Mammei

# The Detector Mount

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Courtesy of R. Mammei



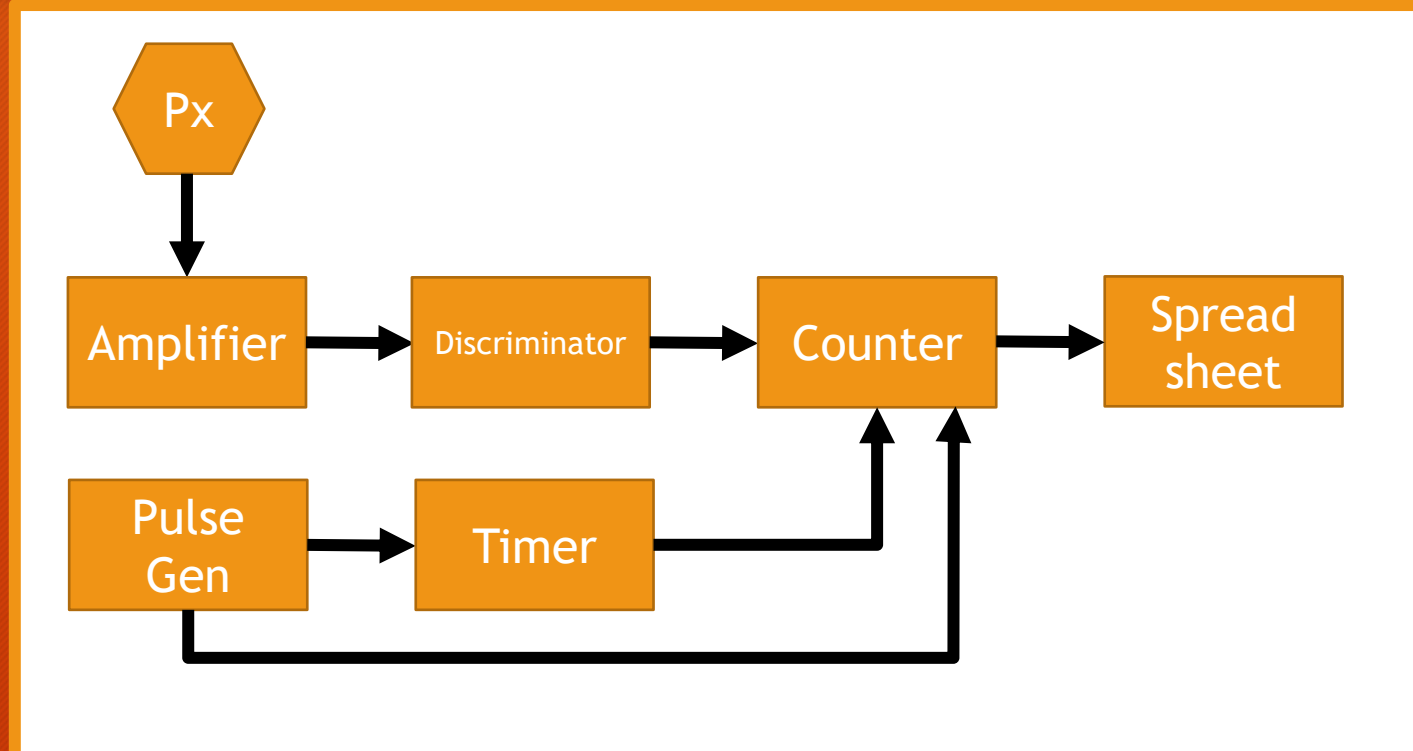
Courtesy of the Nab collaboration



# Proton Spot Size Study

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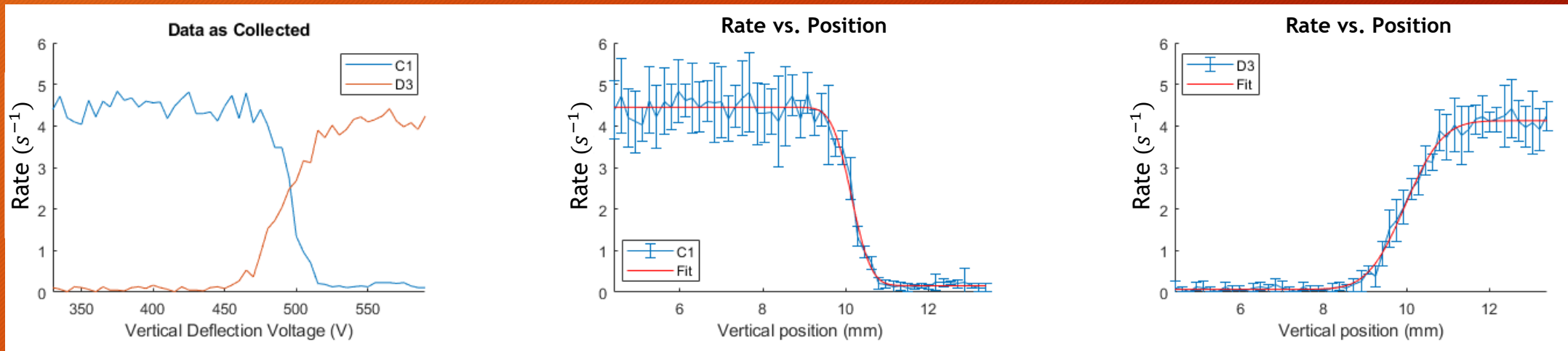
- Use edge of pixel to determine beam diameter ( $1 \pm 0.2\text{mm}$ )
- Erf fit in terms of position
- Two Methods
  - NIM Counter
  - Dedicated DAQ software
- Position information extremely relevant
- Pixel Charge-Sharing Study
  - Much the same as above - now looking at detector with beam



Schematic of the spot size determination using hardware

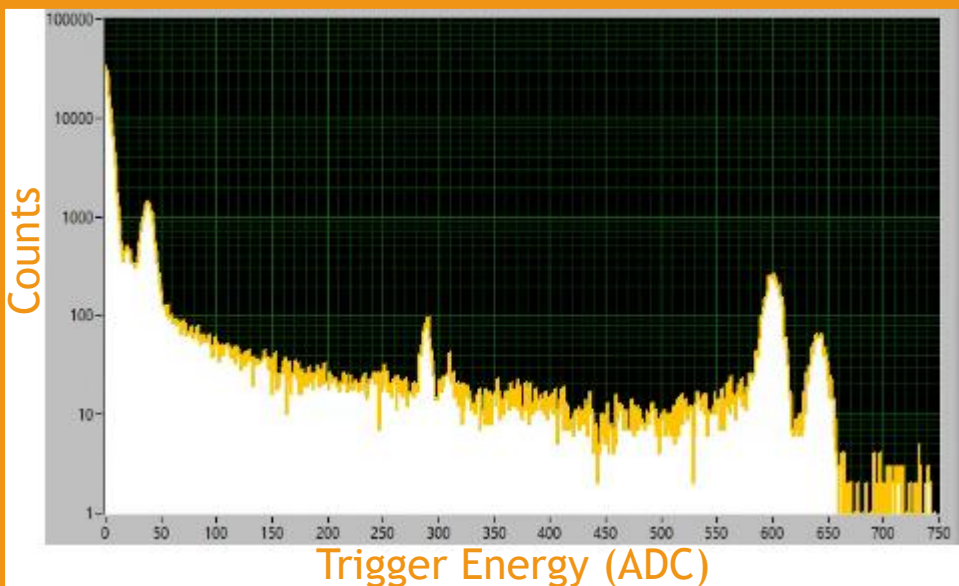
# Statistics for the Counter Method

- Created a MATLAB script to fit a cumulative distribution
  - Assumed displacement was center-to-center distance
  - Extracted 2\*HWHM
- $F(x) = \frac{a}{2} \left[ b \pm \operatorname{erf} \left( \frac{x-\mu}{\sqrt{2}\sigma} \right) \right]$
  - $2 * HWHM = 2\sqrt{2 \ln 2} \sigma$
  - Corresponds to beam cross-section



# Running Parameter Optimization

- Two kinds of detectors:  
P-spray and P-stop
- Intend to characterize both with 30KeV protons and radiation sources ( $Cd^{109}$  and  $Sn^{113}$ )



- Want to reduce typical noise contributions
  - Thermal (Johnson) noise  $\propto I_L$ 
    - Temperature and bias are coupled
    - $I_L \propto T^2 \exp\left(-\frac{E_g}{2kT}\right)$
    - Use of  $LN_2$  to achieve temperatures of 120°K
  - Shot noise - FET amplifier
  - $1/f$  (“pink”) noise
- Analysis is in-progress

Thank you!

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